## Densification, Creep and Oxidation Behavior of ZrB<sub>2</sub>-SiC Based Ultra-High Temperature Ceramic Composites

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## ABSTRACT

ZrB2-SiC composites are candidate materials for use in thermal protection systems for leading edges and nose-cones of hypersonic vehicles. Densification of ZrB2 is considered challenging, because of its covalent bonding, which is responsibility for sluggish rate of lattice diffusion. It has been noticed that addition of 20 vol% SiC not only improves the creep and oxidation resistance in air by formation of a protective scale borosilicate glass, but also densification by inhibiting grain growth. Whereas densification and oxidation resistance are improved by addition of Si<sub>3</sub>N<sub>4</sub>, creep resistance is adversely affected due to increased grain boundary sliding. Further, the oxide scale evolved during creep at 1300°C is found to be thicker than that developed by isothermal exposure for similar duration. Furthermore, it has been observed that the use of additives like B<sub>4</sub>C and C along with LaB<sub>6</sub> aid in densification by reduction of interfacial impurity oxides, which promote grain growth. Investigations on the ZrB2-SiC composites with 7, 10 and 14 vol% LaB6 have shown that both densification and oxidation resistance scale with the amount of  $LaB_6$  due to its role as oxygen scavenger and formation of protective scale, respectively. It has been observed that dislocation creep has been found to have a significant role in densification of the ZrB<sub>2</sub>-SiC-LaB<sub>6</sub> composites. Further, the creep of the ZrB<sub>2</sub>-SiC-LaB<sub>6</sub> composites at 1300°C appears to be controlled by grain boundary diffusion for the composites with 7 or 10 vol% LaB<sub>6</sub>, and by dislocation glide for that with 14 vol% SiC. The difference between the operating mechanisms of creep is found to be related to the purity of the  $ZrB_2$ matrix grain boundaries as well as ZrB<sub>2</sub>-SiC interfaces.

